

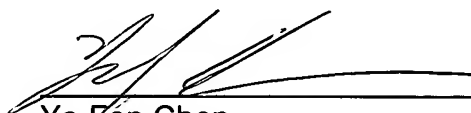


The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

Applicants certify that all references submitted with this disclosure were first cited in a communication from a foreign patent office dated January 4, 2005, which communication is enclosed, not more than three months prior to the filing of this **Supplemental** Information Disclosure Statement.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/8539/BTP.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Ya-Fen Chen', is written over a horizontal line.

Ya-Fen Chen  
Registration No. 51,553  
MOSER, PATTERSON & SHERIDAN, L.L.P.  
3040 Post Oak Blvd. Suite 1500  
Houston, TX 77056  
Telephone: (713) 623-4844  
Facsimile: (713) 623-4846  
Attorney for Applicant(s)



PTO/SB/08b(08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number

Substitute for form 1449/PTO

**SUPPLEMENTAL  
INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet 1 of 1

**Complete if Known**

Application Number	10/683,937
Filing Date	October 10, 2003
First Named Inventor	Kim et al.
Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	AMAT/8539/TSG/EPI/RKK

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	C1	Article by Uchino et al., entitled "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1-µm CMOS ULSIs", IEDM, December 1997, Technical Digest, pgs. 479-482.	
	C2	Article by Sedgwick et al., entitled "Selective SiGe and heavily as doped Si deposited at low temperature by atmospheric pressure chemical vapor deposition", Journal of Vacuum Science & Technology, May/June 1993, No. 3, pgs. 1124-1128.	
	C3	Article by Kamins et al., entitled "Kinetics of Selective epitaxial deposition Si <sub>1-x</sub> Ge <sub>x</sub> ", American Institute of Physics, 1992/August, No. 6, pgs. 669-671	
	C4	Article by Menon et al., entitled "Loading effect in SiGe layers grown by dichlorosilane- and silane-based epitaxy", American Institute of Physics, 2001/November, Volume 90. No. 9, pgs. 4805-4809.	
	C5		
	C6		
	C7		
	C8		
	C9		
	C10		
	C11		
	C12		
	C13		

Examiner  
SignatureDate  
Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.